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Attorney Docket No.: 5308-413

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Saxler et al.

Confirmation No.: 9882

Application No.: 10/849,617

Group Art Unit: 2811

Filed: May 20, 2004

Examiner: Unknown

For: METHODS OF FABRICATING NITRIDE-BASED TRANSISTORS HAVING
REGROWN OHMIC CONTACT REGIONS AND NITRIDE-BASED
TRANSISTORS HAVING REGROWN OHMIC CONTACT REGIONS

Date: January 25, 2005

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

PRELIMINARY AMENDMENT

Sir:

Applicant provides the present Preliminary Amendment to correct typographic errors in the present application.

Amendments to the specification begin on page 2 of this paper.